MAC210A8FP, MAC210A10FP

Triacs

Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
- Ⓤ Indicates UL Registered — File #E69369
- Device Marking: Logo, Device Type, e.g., MAC210A8FP, Date Code

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off–State Voltage(1) (T_J = –40 to +125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC210A8FP MAC210A10FP	V_{DRM}, V_{RRM}	 600 800	Volts
On-State RMS Current (T_C = +70°C)(2) Full Cycle Sine Wave 50 to 60 Hz	$I_{T(RMS)}$	10	Amps
Peak Non–repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T_C = +70°C) Preceded and followed by rated current	I_{TSM}	100	Amps
Circuit Fusing Consideration (t = 8.3 ms)	I^2t	40	A^2s
Peak Gate Power (T_C = +70°C, Pulse Width = 10 μs)	P_{GM}	20	Watts
Average Gate Power (T_C = +70°C, t = 8.3 ms)	$P_{G(AV)}$	0.35	Watt
Peak Gate Current (T_C = +70°C, Pulse Width = 10 μsec)	I_{GM}	2.0	Amps
RMS Isolation Voltage (T_A = 25°C, Relative Humidity ⩽ 20%) Ⓤ	$V_{(ISO)}$	1500	Volts
Operating Junction Temperature Range	T_J	–40 to +125	°C
Storage Temperature Range	T_{stg}	–40 to +150	°C

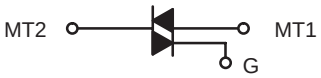
(1) V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

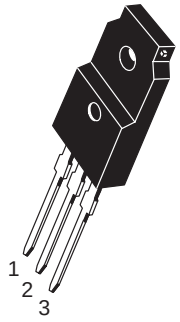
(2) The case temperature reference point for all T_C measurements is a point on the center lead of the package as close as possible to the plastic body.

ON Semiconductor

http://onsemi.com

ISOLATED TRIAC Ⓤ
10 AMPERES RMS
600 thru 800 VOLTS





ISOLATED TO–220 Full Pack
CASE 221C
STYLE 3

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate

ORDERING INFORMATION

Device	Package	Shipping
MAC210A8FP	ISOLATED TO220FP	500/Box
MAC210A10FP	ISOLATED TO220FP	500/Box

THERMAL CHARACTERISTICS

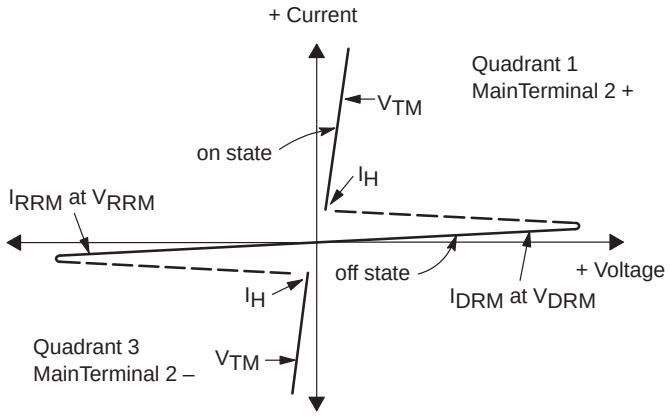
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8″ from Case for 10 Seconds	T_L	260	°C

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted; Electricals apply in both directions)

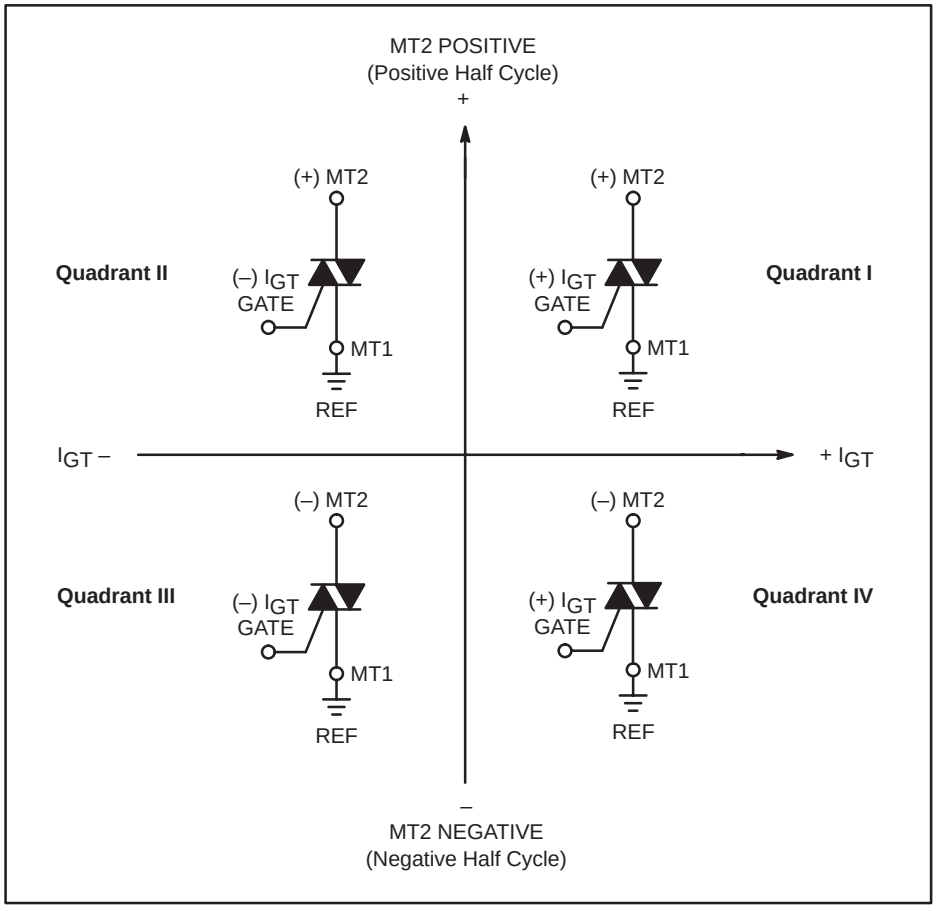
Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Peak Repetitive Blocking Current (V_D = Rated V_{DRM}, V_{RRM}; Gate Open)	T_J = 25°C T_J = +125°C	I_{DRM}, I_{RRM}	— —	— —	10 2.0	μA mA
ON CHARACTERISTICS						
Peak On-State Voltage (I_{TM} = ±14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle ≤ 2%)		V_{TM}	—	1.2	1.65	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms)		I_{GT}				mA
MT2(+), G(+)			—	12	50	
MT2(+), G(–)			—	12	50	
MT2(–), G(–)			—	20	50	
MT2(–), G(+)			—	35	75	
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, R_L = 100 Ohms)		V_{GT}				Volts
MT2(+), G(+)			—	0.9	2.0	
MT2(+), G(–)			—	0.9	2.0	
MT2(–), G(–)			—	1.1	2.0	
MT2(–), G(+)			—	1.4	2.5	
Gate Non–Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 V, R_L = 100 Ω, T_J = +125°C) All Four Quadrants		V_{GD}	0.2	—	—	Volts
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = ±200 mA)		I_H	—	6.0	50	mA
Turn-On Time (Rated V_{DRM}, I_{TM} = 14 A, I_{GT} = 120 mA, Rise Time = 0.1 μs, Pulse Width = 2 μs)		t_{gt}	—	1.5	—	μs
DYNAMIC CHARACTERISTICS						
Critical Rate of Rise of Commutation Voltage (V_D = Rated V_{DRM}, I_{TM} = 14 A, Commutating di/dt = 5.0 A/ms, Gate Unenergized, T_C = +70°C)		$dv/dt_{(c)}$	—	5.0	—	V/μs
Critical Rate of Rise of Off–State Voltage (V_D = Rated V_{DRM}, Exponential Voltage Rise, Gate Open, T_C = +70°C)		dv/dt	—	100	—	V/μs

Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
V_{DRM}	Peak Repetitive Forward Off State Voltage
I_{DRM}	Peak Forward Blocking Current
V_{RRM}	Peak Repetitive Reverse Off State Voltage
I_{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I_H	Holding Current



Quadrant Definitions for a Triac



All polarities are referenced to MT1.
With in–phase signals (using standard AC lines) quadrants I and III are used.

TYPICAL CHARACTERISTICS

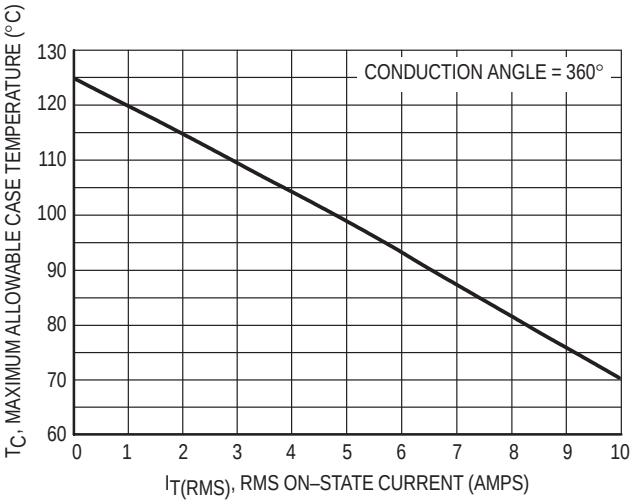


Figure 1. Current Derating

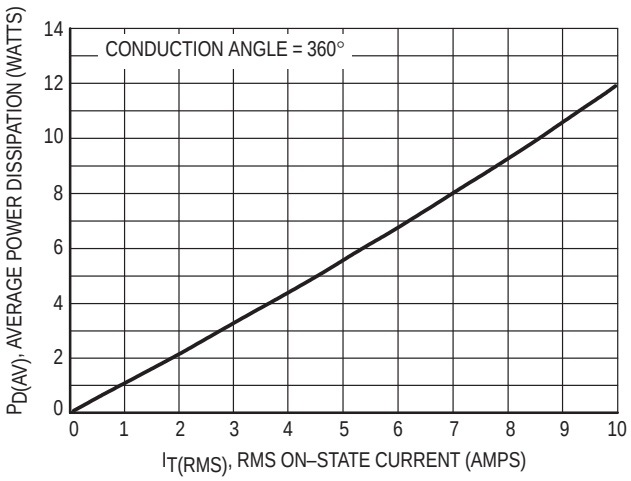


Figure 2. Power Dissipation

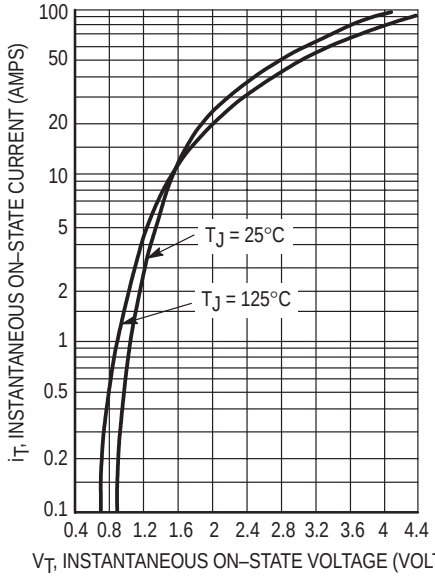


Figure 3. Maximum On–State Characteristics

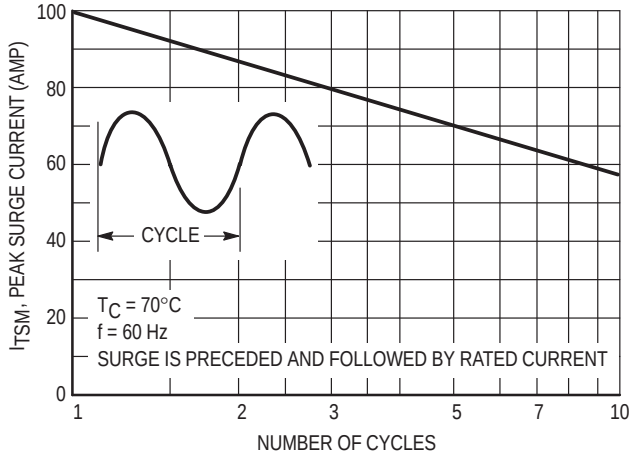


Figure 4. Maximum Nonrepetitive Surge Current

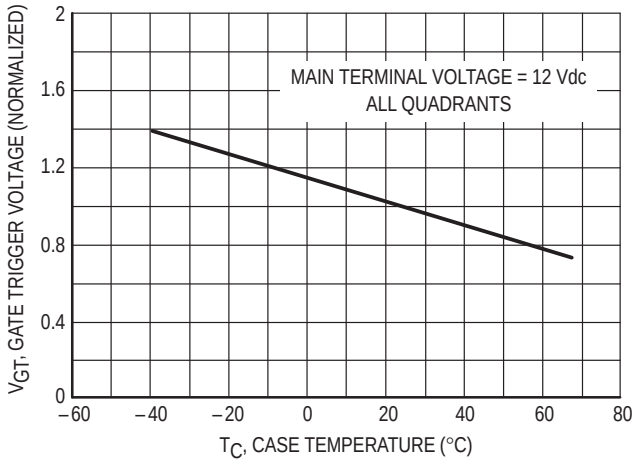


Figure 5. Typical Gate Trigger Voltage

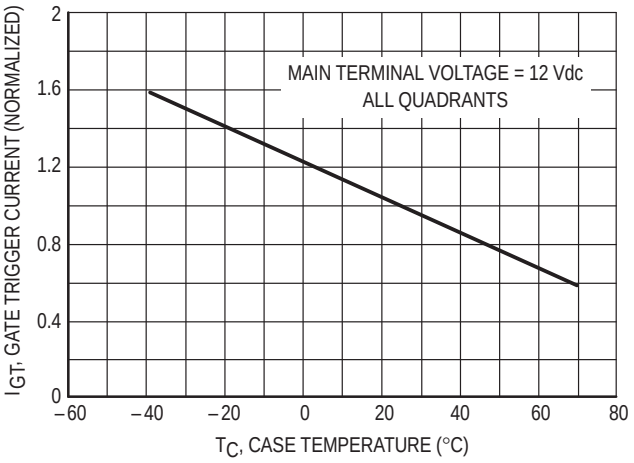


Figure 6. Typical Gate Trigger Current

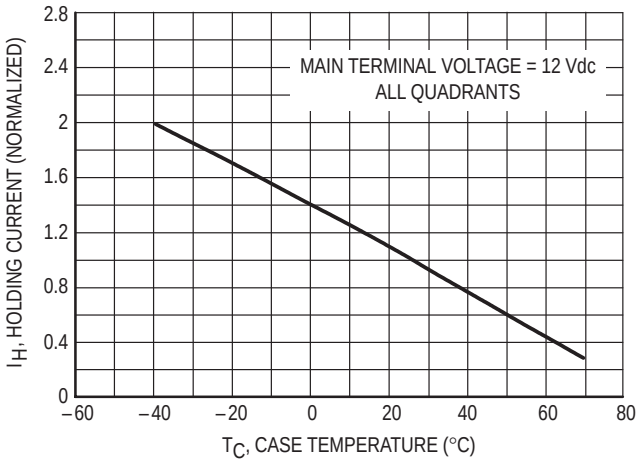


Figure 7. Typical Holding Current

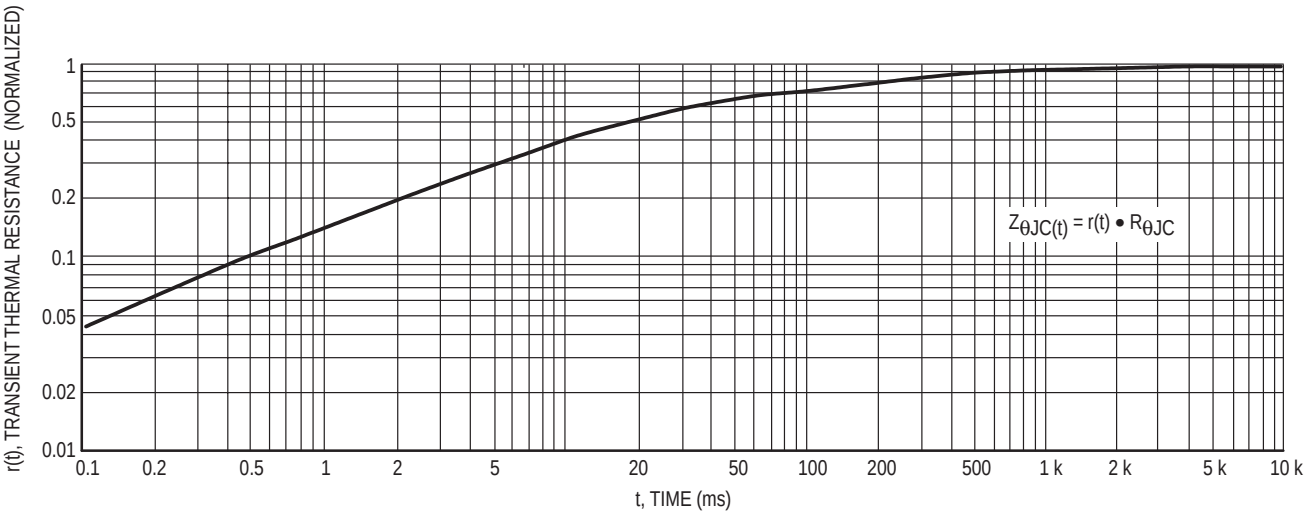
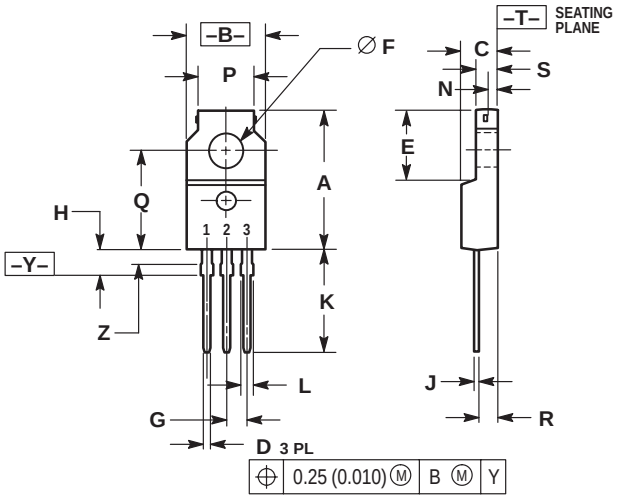


Figure 8. Thermal Response

PACKAGE DIMENSIONS

ISOLATED TO–220 Full Pack
CASE 221C–02
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	—	1.25	—
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

STYLE 3:
PIN 1. MT 1
2. MT 2
3. GATE

Notes

PUBLICATION ORDERING INFORMATION

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